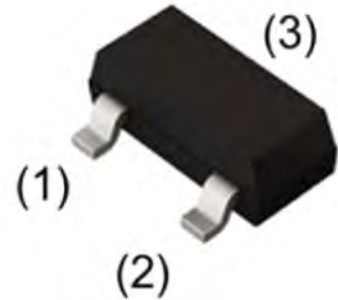
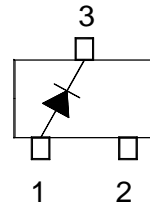


SILICON EPITAXIAL PLANAR SCHOTTKY BARRIER DIODE

for low power rectification and switching power supply

Features

- Small surface mounting type.
- High reliability.




SOT-23 Plastic Package

Marking

Marking Code: **FE**

Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Value	Unit
Peak Reverse Voltage	V_{RM}	40	V
DC Reverse Voltage	V_R	20	V
Mean Rectifying Current	I_o	0.5	A
Peak Forward Surge Current ¹⁾	I_{FSM}	3	A
Junction Temperature	T_j	125	$^\circ\text{C}$
Storage Temperature Range	T_s	-40 to +125	$^\circ\text{C}$

¹⁾ 60Hz for 1 

Characteristics at $T_a = 25^\circ\text{C}$

Parameter	Symbol	Min	Typ	Max	Unit
Forward Voltage at $I_F = 10\text{mA}$ at $I_F = 500\text{mA}$	V_F	-	-	0.3 0.5	V
Reverse Current at $V_R = 10\text{V}$	I_R	-	-	30	μA
Capacitance Between Terminals at $V_R = 10\text{V}$, $f = 1\text{MHz}$	C_T	-	20	-	pF

● Electrical characteristic curves ($T_a = 25^\circ\text{C}$)

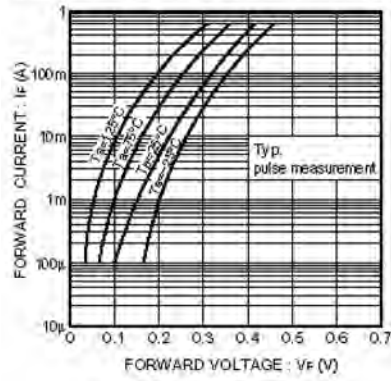


Fig. 1 Forward characteristics

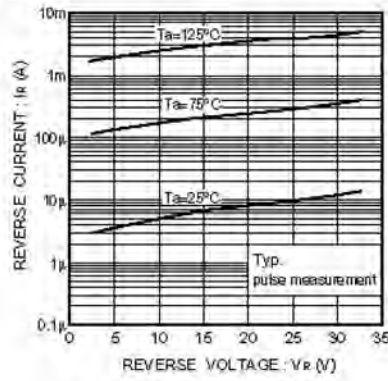


Fig. 2 Reverse characteristics

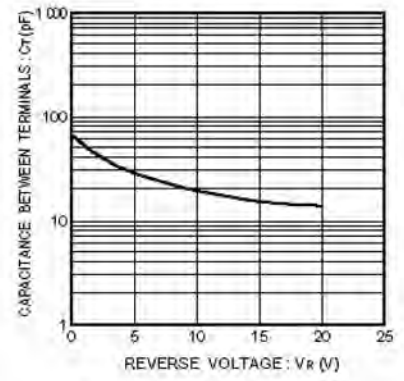
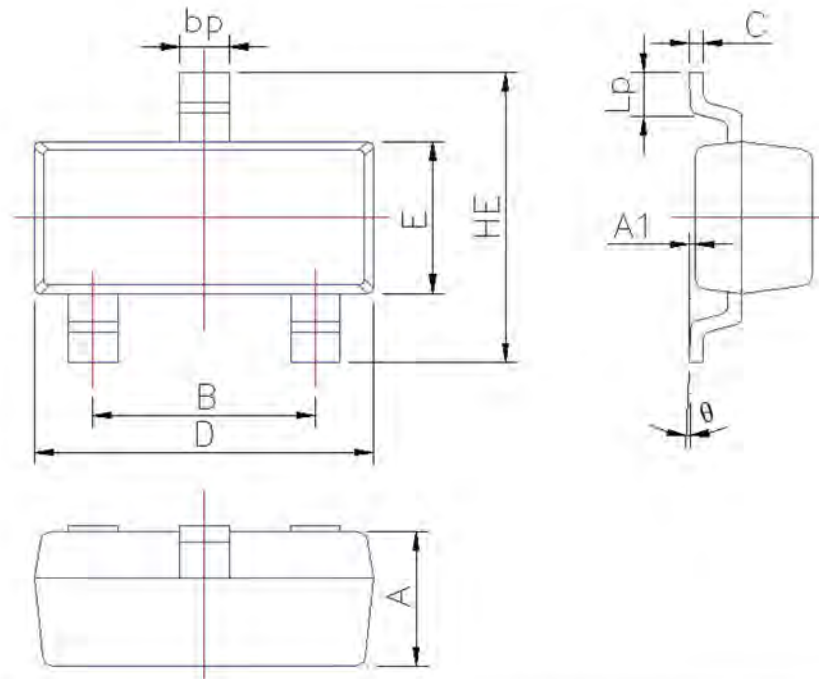


Fig. 3 Capacitance between terminals characteristic

PACKAGE OUTLINE

Plastic surface mounted package; 3 leads

SOT-23



Symbol	Dimension in Millimeters	
	Min	Max
A	0.90	1.10
A1	0.013	0.100
B	1.80	2.00
bp	0.35	0.50
C	0.09	0.150
D	2.80	3.00
E	1.20	1.40
HE	2.20	2.80
Lp	0.20	0.50
θ	0°	5°